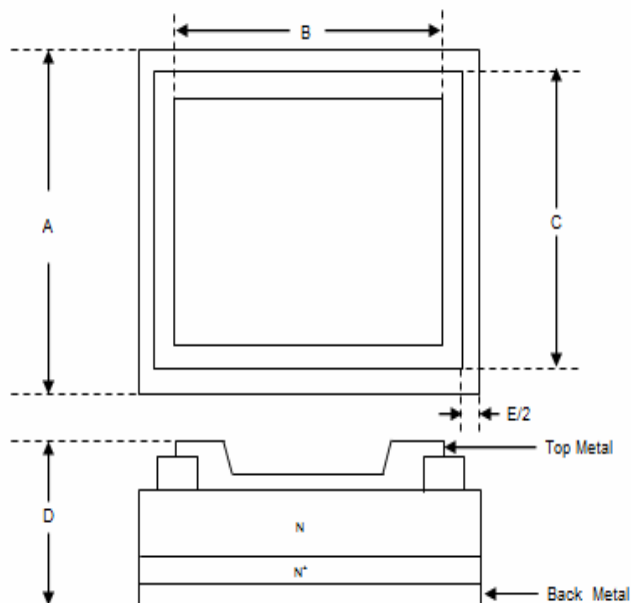


Trench Schottky Barrier Diode Wafer (TSBD)



Item	Dimensions	
	um	mil
Die Size (A)	1925	75
Top Metal Pad Size (B)	1825	71.9
Passivation Seal (C)	1855	73.0
Wafer Thickness (D)	260	10.2
Scribe Line Width (E)	70	2.76
Other Informations		
Wafer Size	6"	
Gross Die	4300	
Top Metal	Ag	
Back Metal	Ag	

Electrical Characteristics @TA=25°C

Item	Symbol	Spec. Limit	Die Sort	Unit
Maximum Repetitive Peak Reverse Voltage @0.2mA	V_{RRM}	100	106	V
Maximum Average Forward Rectified Current	I_O	10	-	A
Forward Voltage Drop, @ $I_F=3A$ @ $I_F=5A$ @ $I_F=10A$	V_F	- 0.59 0.75	0.53 -	V
Maximum Reverse Current at Rated V_{RRM}	I_R	40	15	μA
Peak Forward Surge Current, 8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC Method)	I_{FSM}	120	-	A
Operating Temperature Range	T_J	-50 to +150	-	°C
Storage Temperature Range	T_{STG}	-50 to +150	-	°C